

ESD and Surge Protection Device

Low Capacitance Surge Protection for High Speed Data

SZNSP8814L

The SZNSP8814L surge protector is designed specifically to protect 10/100 and GbE Ethernet signals from high levels of surge current. Low clamping voltage under high surge conditions make this device an ideal solution for protecting voltage sensitive lines leading to Ethernet transceiver chips. Low capacitance combined with flow-through style packaging allows for easy PCB layout and matched trace lengths necessary to maintain consistent impedance between high-speed differential lines.

Features

- Protection for the Following IEC Standards:
IEC 61000-4-2 (ESD) ± 30 kV (Contact)
IEC 61000-4-5 (Lightning) 35 A (8/20 μ s)
- Flow-Thru Routing Scheme
- Low Capacitance: 2 pF Max (I/O to I/O)
- UL Flammability Rating of 94 V-0
- Wettable Flank Package for optimal Automated Optical Inspection (AOI)
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable*
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

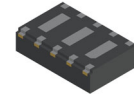
- In Vehicle Networking (IVN)
- Open Alliance BroadR-Reach (OABR)

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Power Dissipation 8/20 Double Exponential Waveform	P_{PK}	562	W
Operating Junction Temperature Range	T_J	-55 to +150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$
Lead Solder Temperature - Maximum (10 Seconds)	T_L	260	$^\circ\text{C}$
Human Body Model (HBM) IEC 61000-4-2 Contact (ESD) IEC 61000-4-2 Air (ESD) ISO 10605 330 pF / 330 Ω Contact ISO 10605 330 pF / 2 k Ω Contact ISO 10605 150 pF / 2 k Ω Contact	ESD	± 8 ± 30 ± 30 ± 30 ± 30	kV
Maximum Peak Pulse Current 8/20 μ s @ $T_A = 25^\circ\text{C}$ 10/700 μ s @ $T_A = 25^\circ\text{C}$	I_{PP}	35 14	A

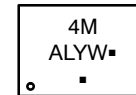
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

See Application Note [AND8308/D](#) for further description of survivability specs.



WDFNW10
CASE 515AL

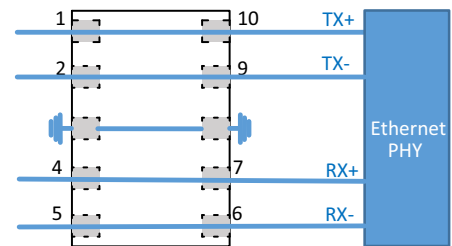
MARKING DIAGRAM



- 4M = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

TYPICAL APPLICATION

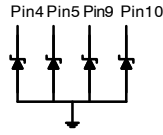
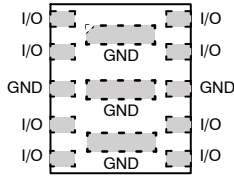


ORDERING INFORMATION

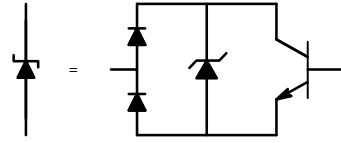
Device	Package	Shipping†
SZNSP8814LMTWTAG	WDFNW10 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

SZNSP8814L



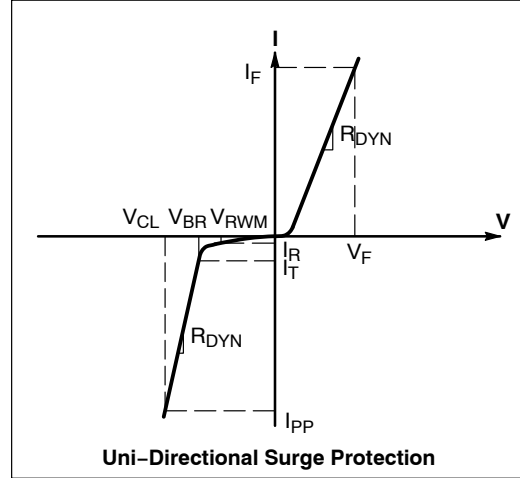
Pin Schematic



ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

Symbol	Parameter
V _{RWM}	Working Peak Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I _T
I _T	Test Current
V _{HOLD}	Holding Reverse Voltage
I _{HOLD}	Holding Reverse Current
R _{DYN}	Dynamic Resistance
I _{PP}	Maximum Peak Pulse Current
V _C	Clamping Voltage @ I _{PP} V _C = V _{HOLD} + (I _{PP} * R _{DYN})
I _F	Forward Current
V _F	Forward Voltage @ I _F



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{RWM}	Reverse Working Voltage	Any I/O to GND (Note 1)			3.0	V
V _F	Forward Voltage	I _F = 10 mA, GND to All IO Pins	0.5	0.85	1.1	V
V _{BR}	Breakdown Voltage	I _T = 1 mA, I/O to GND	3.2	3.5	5.0	V
I _R	Reverse Leakage Current	V _{RWM} = 3.0 V, I/O to GND			0.5	μA
V _C	Clamping Voltage (Note 2)	I _{PP} = 1 A I _{PP} = 10 A I _{PP} = 25 A I _{PP} = 35 A		4.0 6.0 8.0 10	5.0 6.5 10 15	V
V _C	Clamping Voltage	IEC61000-4-2, ±8 kV Contact	See Figures 7 and 8			
C _J	Junction Capacitance	V _R = 0 V, f = 1 MHz between I/O Pins		1.5	2.0	pF
		V _R = 0 V, f = 1 MHz between I/O Pins and GND			5.0	
I _L	Insertion Loss	f = 1 GHz		-1		dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Surge protection devices are normally selected according to the working peak reverse voltage (V_{RWM}), which should be equal or greater than the DC or continuous peak operating voltage level.
- Any I/O to GND (8/20 μs pulse).

TYPICAL CHARACTERISTICS

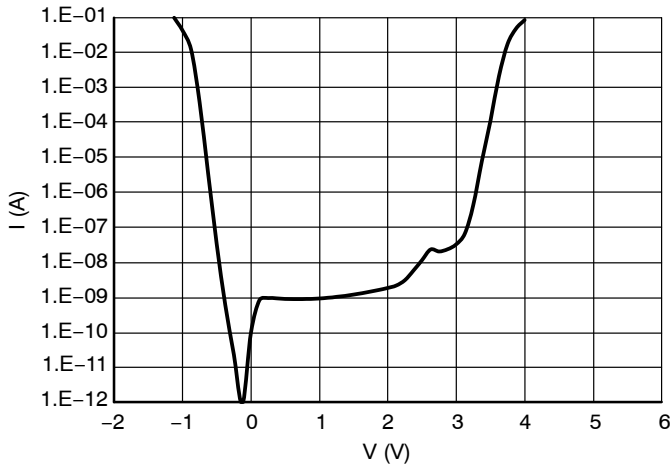


Figure 1. IV Characteristics

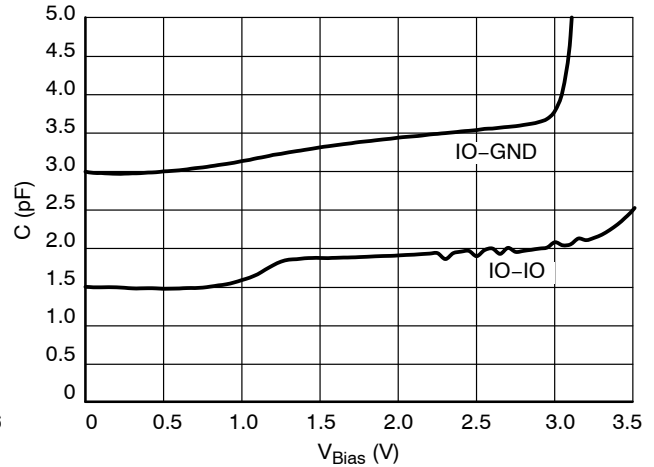


Figure 2. CV Characteristics

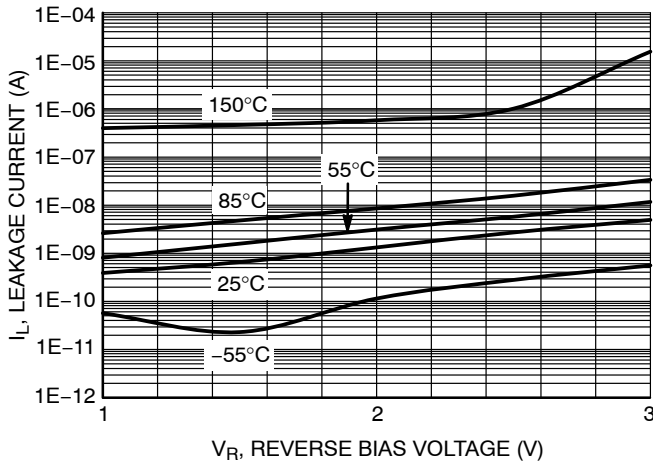


Figure 3. I_R vs. Temperature Characteristics

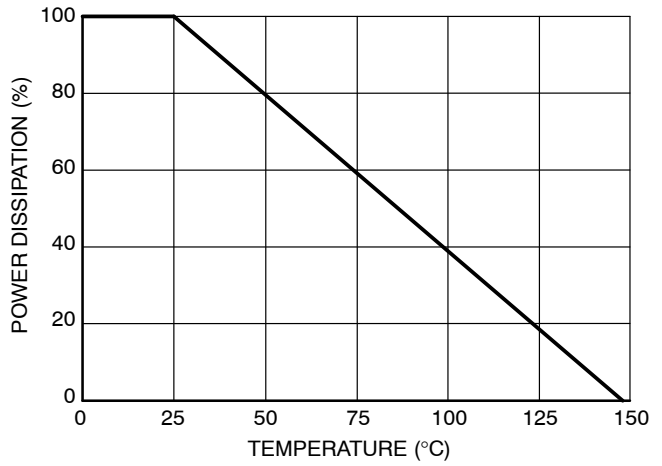


Figure 4. Steady State Power Derating

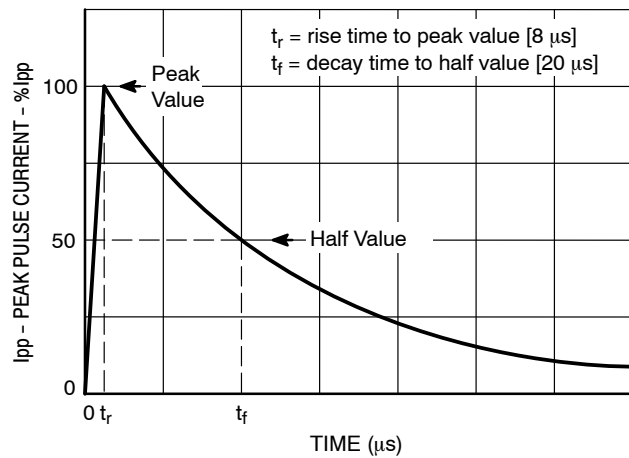


Figure 5. IEC61000-4-5 Pulse Waveform (8/20 μ s)

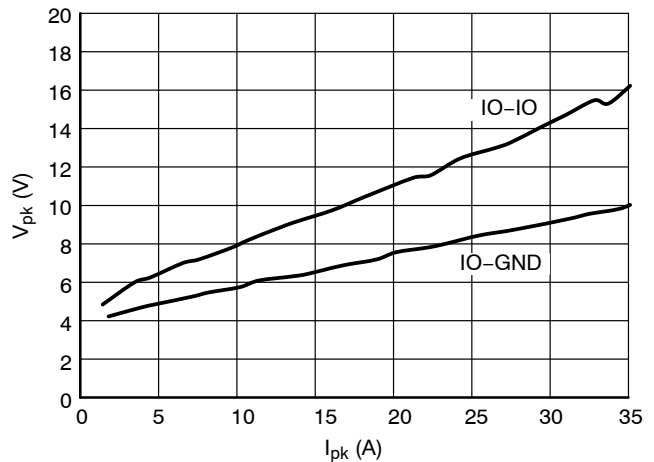


Figure 6. Clamping Voltage vs. Peak Pulse Current (8/20 μ s)

TYPICAL CHARACTERISTICS

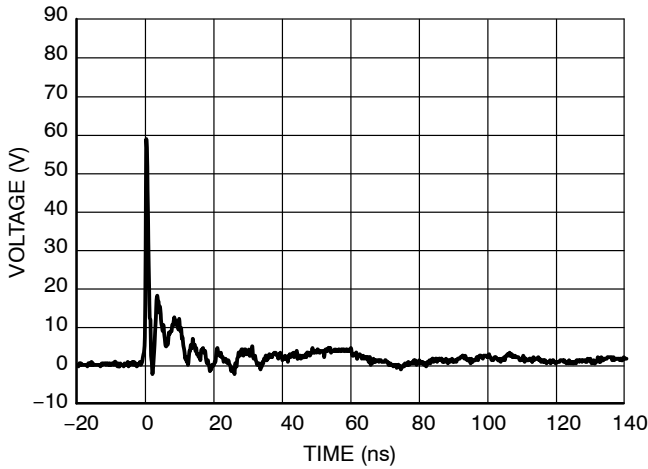


Figure 7. IEC61000-4-2 +8 kV Contact Clamping Voltage

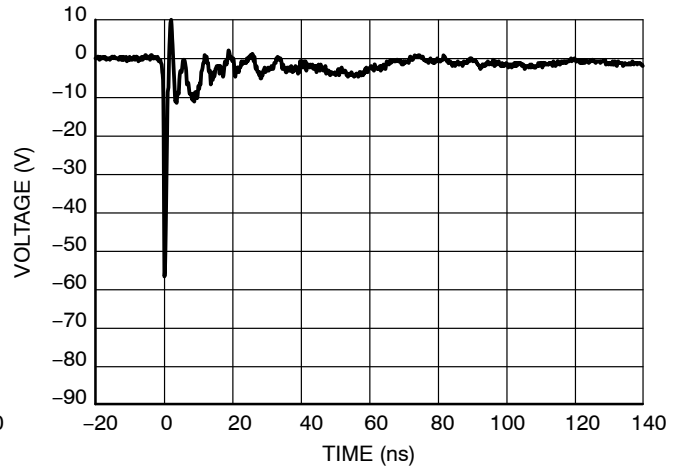


Figure 8. IEC61000-4-2 -8 kV Contact Clamping Voltage

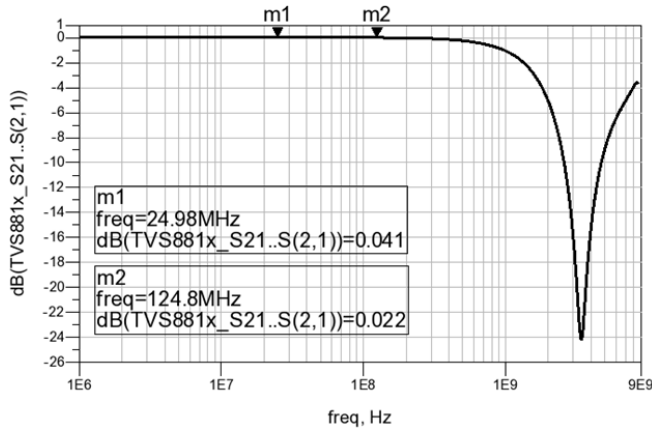


Figure 9. Typical Insertion Loss

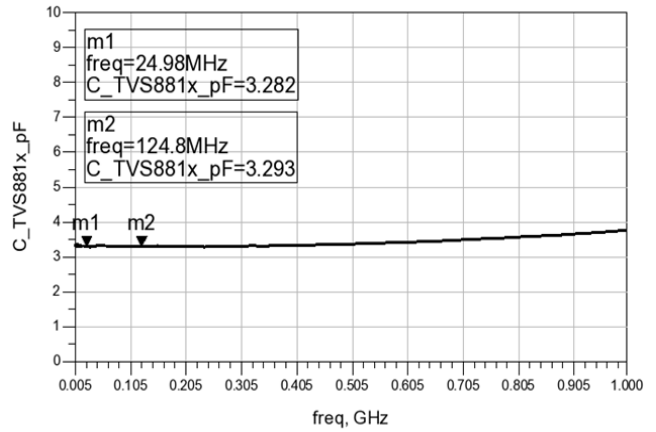


Figure 10. Typical Capacitance vs. Frequency

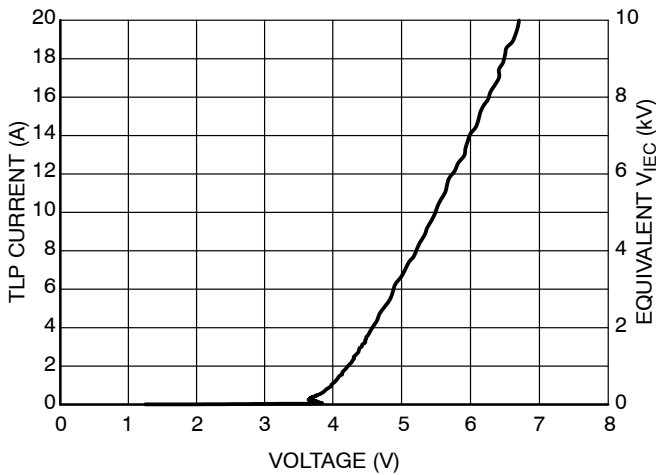


Figure 11. Positive TLP IV Curve

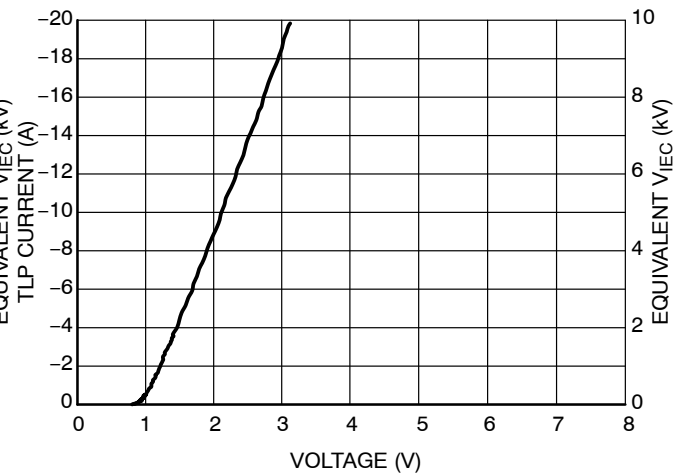
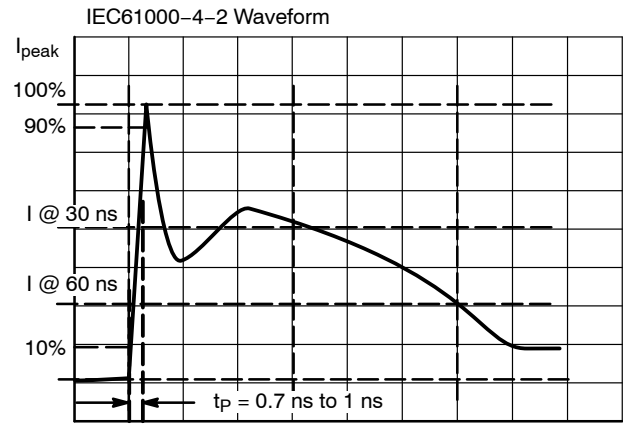


Figure 12. Negative TLP IV Curve

NOTE: TLP parameter: $Z_0 = 50 \Omega$, $t_p = 100 \text{ ns}$, $t_r = 300 \text{ ps}$, averaging window: $t_1 = 30 \text{ ns}$ to $t_2 = 60 \text{ ns}$.

ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000-4-2 waveform. Since the IEC61000-4-2 was written as a pass/fail spec for larger systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.



IEC 61000-4-2 Spec.

Level	Test Voltage (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

Figure 13. IEC61000-4-2 Spec

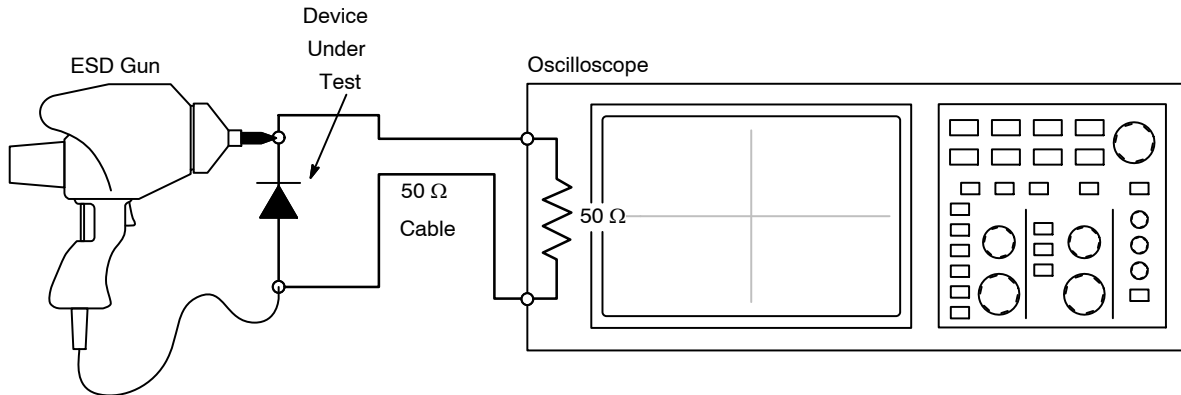


Figure 14. Diagram of ESD Clamping Voltage Test Setup

The following is taken from Application Note
AND8308/D – Interpretation of Datasheet Parameters
for ESD Devices.

Transmission Line Pulse (TLP) Measurement

Transmission Line Pulse (TLP) provides current versus voltage (I–V) curves in which each data point is obtained from a 100 ns long rectangular pulse from a charged transmission line. A simplified schematic of a typical TLP system is shown in Figure 15. TLP I–V curves of ESD protection devices accurately demonstrate the product’s ESD capability because the 10s of amps current levels and under 100 ns time scale match those of an ESD event. This is illustrated in Figure 16 where an 8 kV IEC 61000–4–2 current waveform is compared with TLP current pulses at 8 A and 16 A. A TLP I–V curve shows the voltage at which

the device turns on as well as how well the device clamps voltage over a range of current levels.

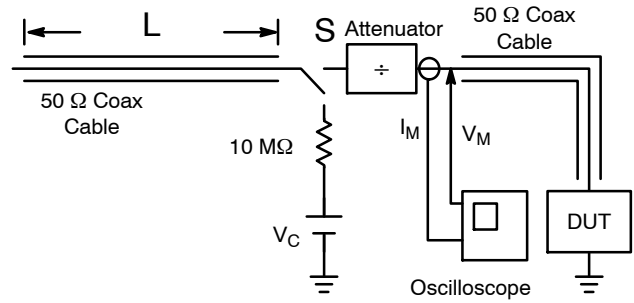


Figure 15. Simplified Schematic of a Typical TLP System

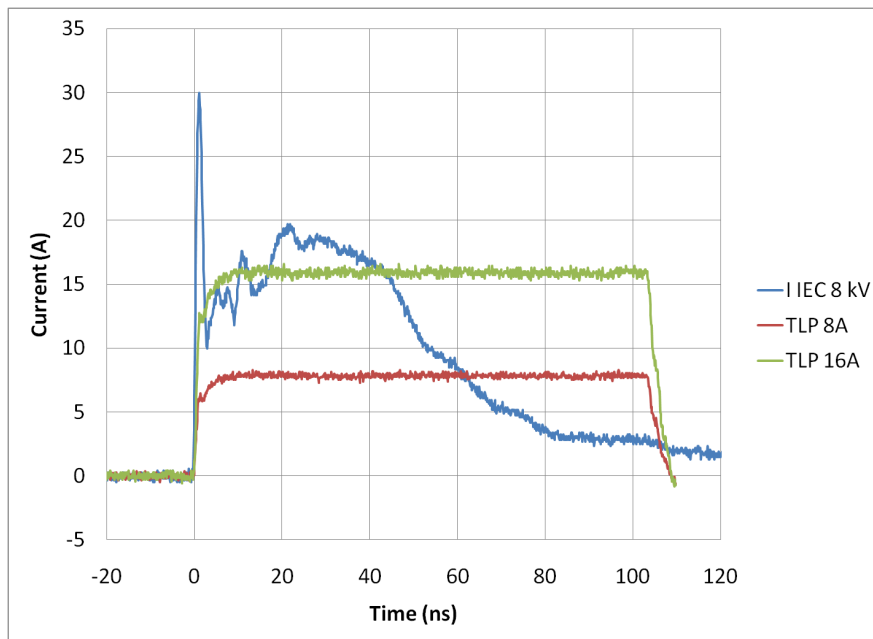
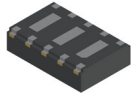
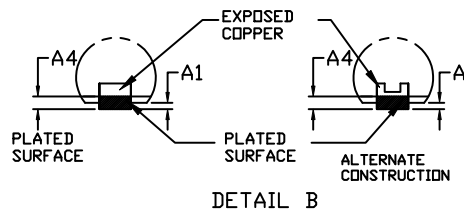
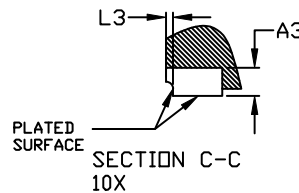
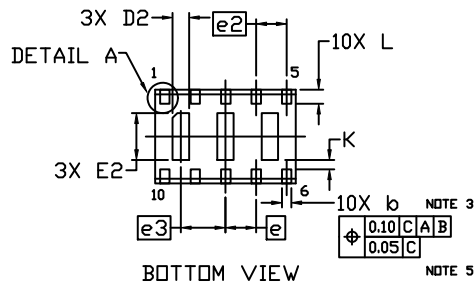
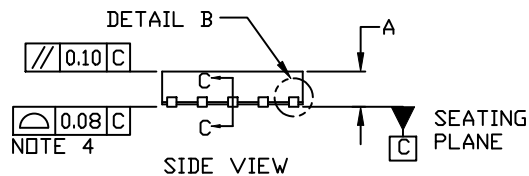
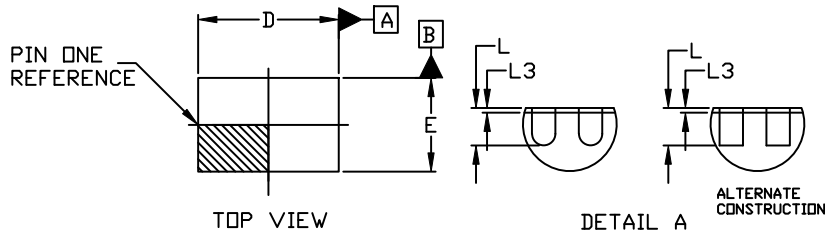
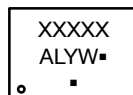


Figure 16. Comparison Between 8 kV IEC 61000–4–2 and 8 A and 16 A TLP Waveforms


WDFNW10 3.0x2.0, 0.65P
CASE 515AL
ISSUE B

DATE 05 FEB 2020


GENERIC
MARKING DIAGRAM*


XXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

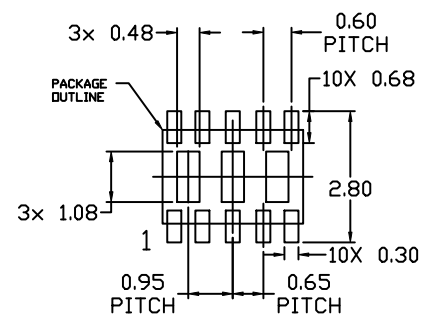
(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION *b* APPLIES TO PLATED TERMINALS AND IS MEASURED BETWEEN 0.15 AND 0.30MM FROM THE TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
5. POSITIONAL TOLERANCE APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
A1	0.00	---	0.05
A3	0.20 REF		
A4	0.10	---	---
b	0.15	0.20	0.25
D	2.90	3.00	3.10
D2	0.25	0.35	0.45
E	1.90	2.00	2.10
E2	0.90	1.00	1.10
e	0.65 BSC		
e2	0.60 BSC		
e3	0.95 BSC		
K	0.20 REF		
L	0.25	0.30	0.35
L3	---	---	0.09


RECOMMENDED
MOUNTING FOOTPRINT

■ For additional information on our Pb-Free strategy and soldering details, please download the [DIP Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D](#).

DOCUMENT NUMBER: 98AON14034H

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DESCRIPTION: WDFNW10 3.0x2.0, 0.65P

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